STRH12P10ESY3

P-channel 100V - 0.265Ω - TO-257AA
Rad-hard low gate charge STripFET™ Power MOSFET

General features

Type	V_{DSS}
STRH12P10ESY3	100V

- Low $R_{DS(on)}$
- Fast switching
- Single event effect (SEE) hardned
- Low total gate charge
- Light weight
- 100% avalanche tested
- Application oriented characterization
- Hermetically sealed
- Heavy ion SOA
- 100kRad TID
- SEL & SEGR with 34Mev/cm²/mg LET ions

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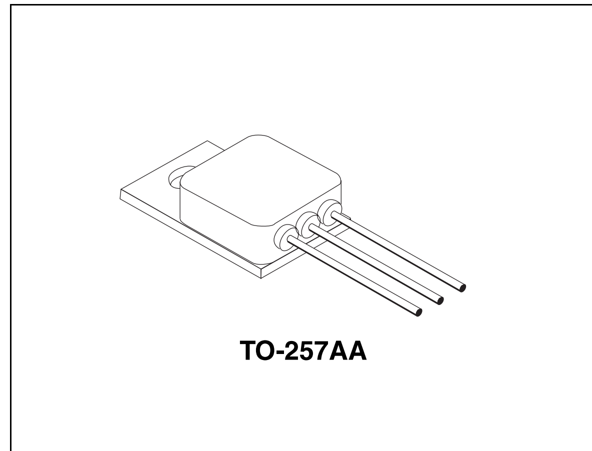
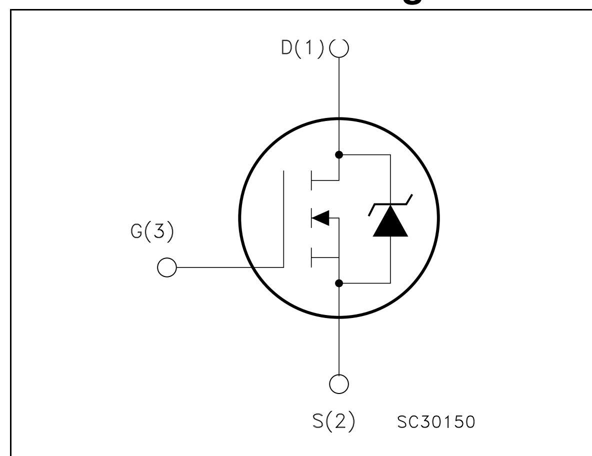

TO-257AA

Internal schematic diagram



Description

This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to sustain high TID and provide immunity to heavy ion effects. It is therefore suitable as power switch in mainly high-efficiency DC-DC converters. It is also intended for any application with low gate charge drive requirements.

Application

- Satellite
- High reliability

Order codes

Part number	Marking	Package	Packaging
STRH12P10ESY1 (1)	RH12P10ESY1	TO-257AA	Individual strip pack
STRH12P10ESY3 (2)	RH12P10ESY3	TO-257AA	Individual strip pack

1. Mil temp range
2. Space flights parts (full ESA flow screening)

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1 Electrical ratings

Table 1. Absolute maximum ratings (pre-irradiation)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	100	V
V_{GS}	Gate-source voltage	±18	V
I_D (1)	Drain current (continuous) at T_C= 25°C	12	A
I_D (1)	Drain current (continuous) at T_C= 100°C	7.5	A
I_{DM} (2)	Drain current (pulsed)	48	A
P_{TOT} (1)	Total dissipation at T_C= 25°C	75	W
dv/dt (3)	Peak diode recovery voltage slope	2.4	V/ns
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Max. operating junction temperature	150	°C

1. Rated according to the Rthj-case + Rthc-s
2. Pulse width limited by safe operating area
3. $I_{SD} \leq$ 12A, di/dt $\leq$ 36A/µs, V_{DD} = 80%$V_{(BR)DSS}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case	1.47	°C/W
Rthc-s	Case-to-sink	0.2	°C/W
Rthj-amb	Thermal resistance junction -amb	62.5	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	6	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, I_D=I_{AR}, V_{DD}=50V)	597	mJ
E_{AR}	Repetitive avalanche	17	mJ

Note: For the P-channel MOSFET actual polarity of voltages and current has to be reversed

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2 Electrical characteristics

(T_{CASE} = 25°C unless otherwise specified)

2.1 Pre-irradiation

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	80% BV_{Dss}			10	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±18V			±100	nA
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS} = 0V	100			V
$V_{GS(th)}$	Gate threshold voltage	V_{DS} =V_{GS}, I_D = 1mA	2		4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 12V, I_D = 12A		0.265	0.3	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25V, f=1MHz, V_{GS}=0V		1303 158 65.6		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 50V, I_D = 6A, V_{GS}=12V		44 4.5 10	62 7 14	nC nC nC
R_G	Gate input resistance	f=1MHz Gate DC Bias=0 Test signal level=20mV open drain		1	2	Ω

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off-delay time Fall time	V_{DD} = 80V, I_D = 12A, R_G = 4.7Ω, V_{GS} = 12V		19 9 37 7		ns ns ns ns

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Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				12 48	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 12A, V_{GS} = 0			1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 12A, di/dt = 100A/µs V_{DD}= 9V, Tj = 25°C		248 2.3 19		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 12A, di/dt = 100A/µs V_{DD}= 9V, Tj = 150°C		300 3 22		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300µs, duty cycle 1.5%

2.2 Post-irradiation

The ST Rad-Hard Power MOSFETs are tested to verify the radiation capability. The technology is extremely resistant to assurance well functioning of the device inside the radiation environments. Every manufacturing lot is tested for total ionizing dose.

(@Tj=25°C up to 100Krad [a])

Table 8. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	80% BV_{Dss}			10	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±18V			±100	nA
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS} = 0V	100			V
$V_{GS(th)}$	Gate threshold voltage	V_{DS} =V_{GS}, I_D = 1mA	2		4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 12V, I_D = 12A		0.265	0.3	Ω

a. According to ESCC 22900 specification, Co60 gamma rays, dose rate:0.1rad/sec.

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Table 9. Single event effect, SOA[1]

Ion	Let (Mev/(mg/cm2))	Energy (MeV)	Range (µm)	V_{DS} (V) @V_{GS}0V
Kr	34	316	43	100
Xe	55.9	459	43	80

1. Rad-Hard Power MOSFETs have been characterized in heavy ion environment for single event effect (SEE). Single event effect characterization is illustrated

Table 10. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD} I_{SDM} [1]	Source-drain current Source-drain current (pulsed)				12 48	A A
V_{SD} [2]	Forward on voltage	I_{SD} = 12A, V_{GS} = 0			1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 12A, di/dt = 100A/µs V_{DD}= 9V, Tj = 25°C		248 2.3 19		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 12A, di/dt = 100A/µs V_{DD}= 9V, Tj = 150°C		300 3 22		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300µs, duty cycle 1.5%

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2.3 Electrical characteristics (curves)

Figure 1. Safe operating area

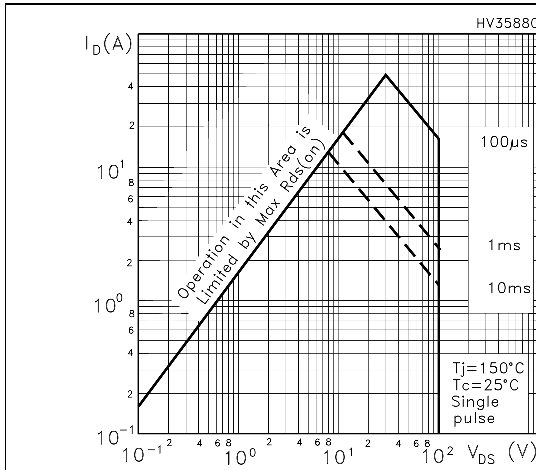

Figure 2. Thermal impedance

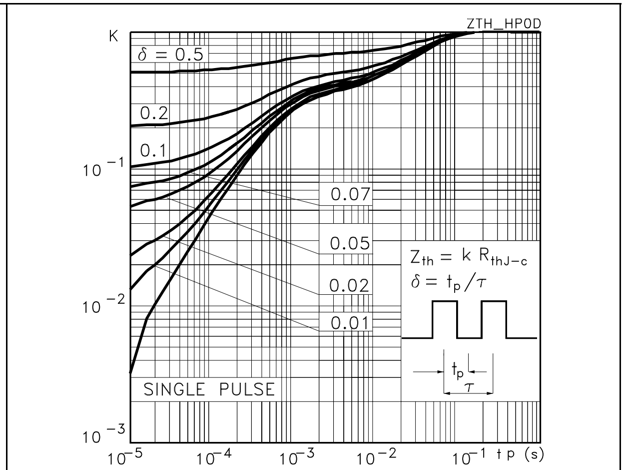

Figure 3. Output characteristics

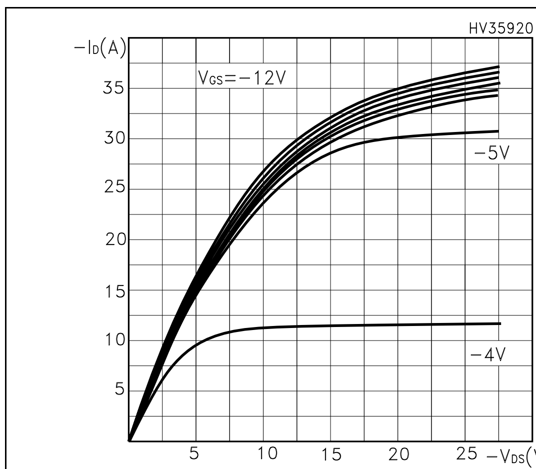

Figure 4. Transfer characteristics

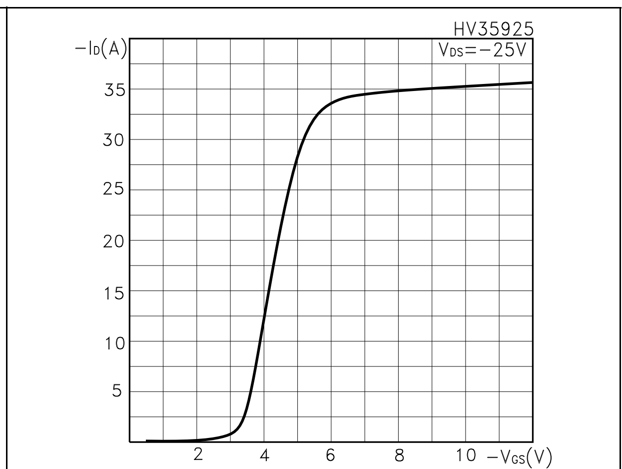

Figure 5. Gate charge vs gate-source voltage

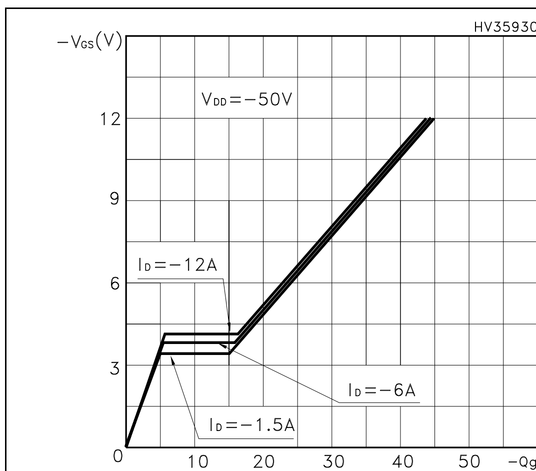

Figure 6. Capacitance variations

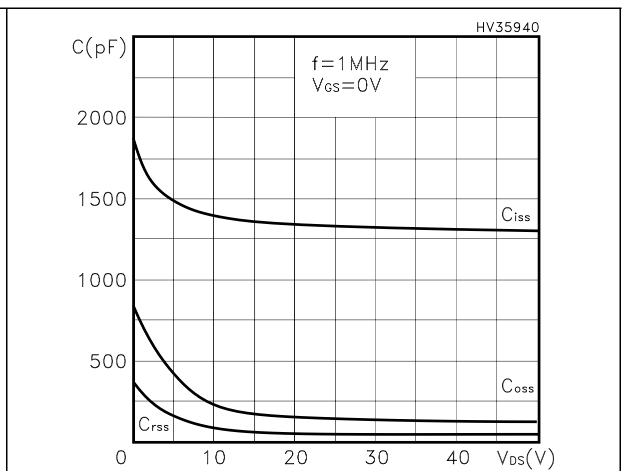

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Figure 7. Normalized BV_{DSS} vs temperature **Figure 8. Static drain-source on resistance**

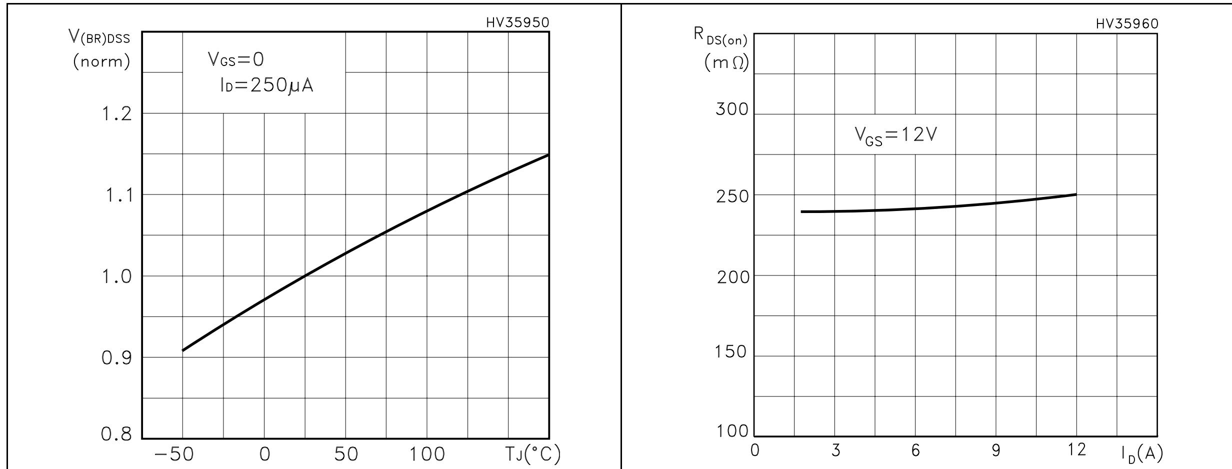


Figure 9. Normalized gate threshold voltage vs temperature **Figure 10. Normalized on resistance vs temperature**

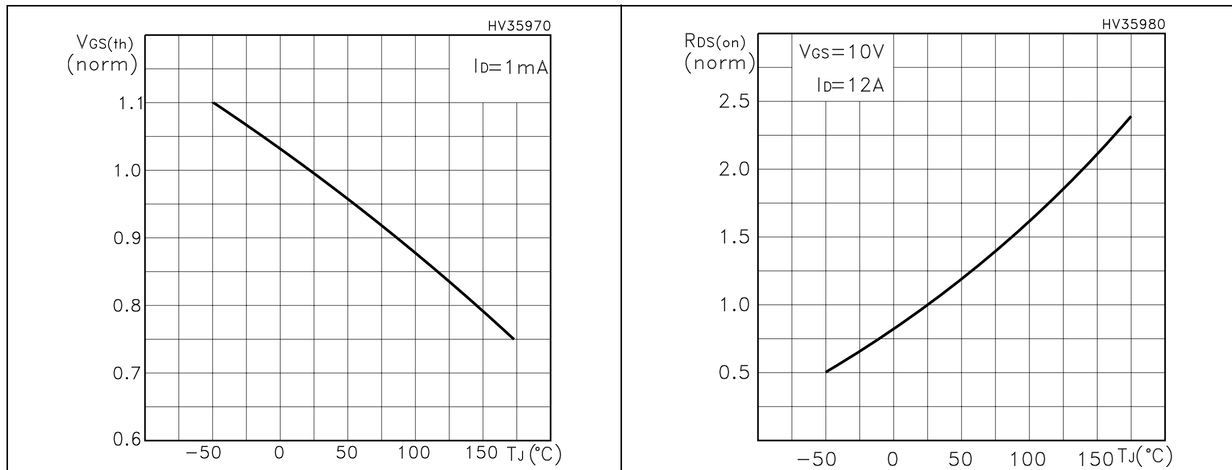
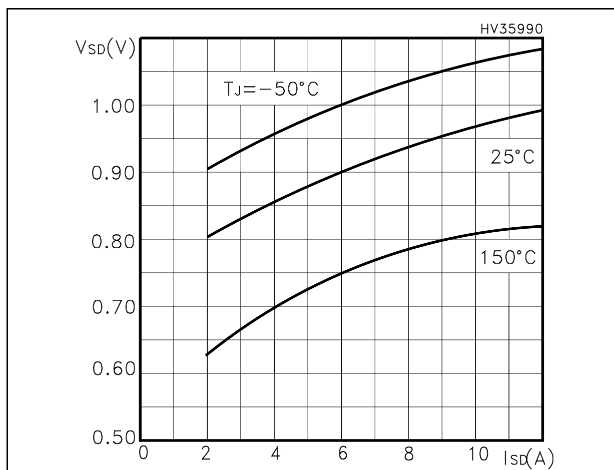


Figure 11. Source drain-diode forward characteristics



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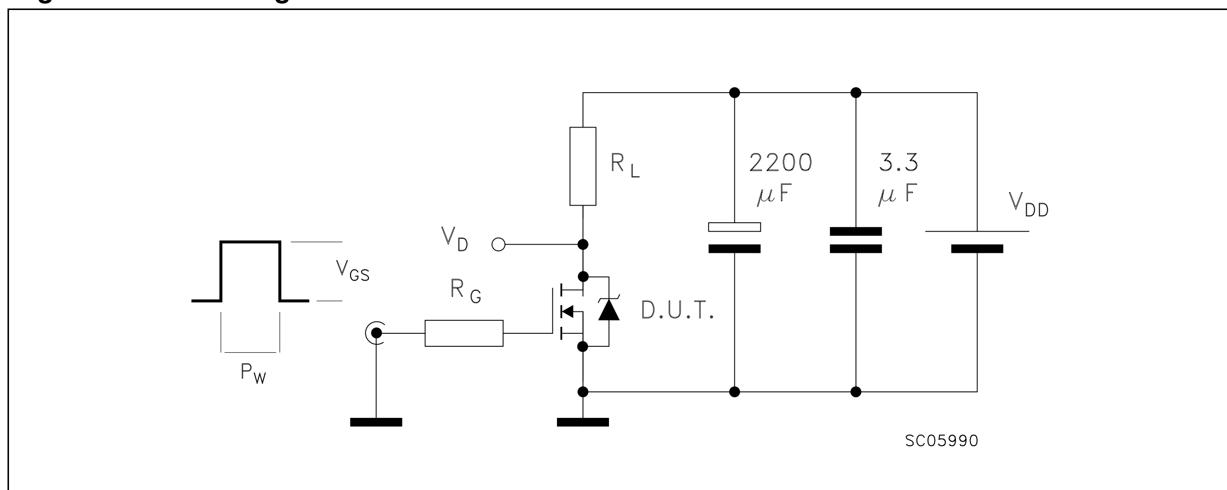
3 Test circuit

Figure 12. Switching times test circuit for resistive load (1)



1. Max driver V_{GS} slope = 1V/ns (no DUT)

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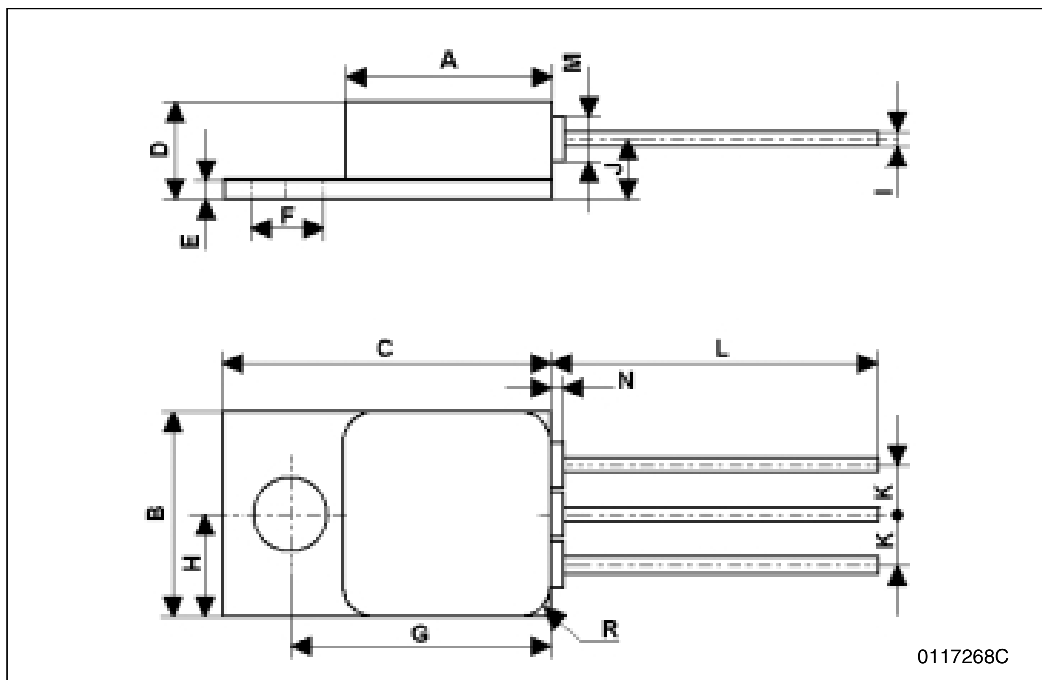
4 Package mechanical data

TO-257AA MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A		10.54			0.415	
B		10.54			0.415	
C		16.64			0.655	
D	4.7		5.33	0.185		0.210
E		1.02			0.40	
F	3.56	3.68	3.81	0.140	0.145	0.150
G		13.51			0.532	
H		5.26			0.207	
I		0.76			0.030	
J		3.05			0.120	
K		2.54			0.100	
L	15.2		16.5	0.598		0.650
M		2.29			0.090	
N			0.71			0.028
R		1.65			0.065	



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5 Revision history

Table 11. Revision history

Date	Revision	Changes
20-Dec-2006	1	First release
19-Mar-2007	2	Complete version

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